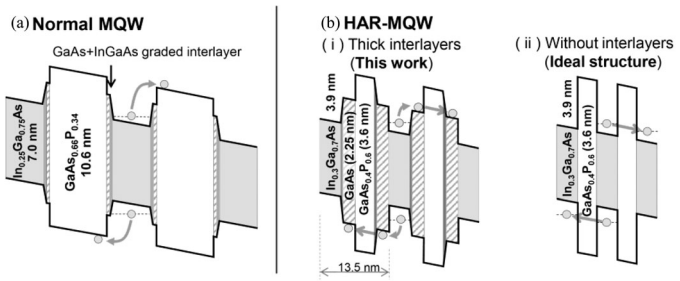
Erratum

Errata to "High-Aspect-Ratio Structures for Efficient Light Absorption and Carrier Transport in InGaAs/GaAsP Multiple Quantum Well Solar Cells"

Hiromasa Fujii, Yunpeng Wang, Kentaroh Watanabe, Masakazu Sugiyama, and Yoshiaki Nakano



sample (periods)	well	barrier
Normal-MQW (40)	$In_{0.25}Ga_{0.75}As$ (7.0 nm) / +1.74%	$GaAs_{0.66}P_{0.34}$ (10.6 nm) / -1.21 %
HAR-MQW (40, 60)	$In_{0.30}Ga_{0.70}As$ (3.9 nm) / +2.08 %	$GaAs_{0.40}P_{0.60}$ (3.6 nm) / -2.23 %

Fig. 2.

We have found several errors in figures in the published article [1].

1) In Fig. 2, the values of the strain are written in the wrong columns. The correct figure is shown here.
2) In Fig. 3, the XRD data for the case without interlayers are incorrect; the plotted data are not for $In_{0.30}Ga_{0.70}As$ (3.9 nm)/$GaAs_{0.40}P_{0.60}$ (3.6 nm), but for $In_{0.30}Ga_{0.70}As$ (4.2 nm)/$GaAs_{0.25}P_{0.75}$ (3.3 nm). The correct plots are shown here. The correct and incorrect plots show similarly degraded XRD patterns, and thus both of them lead to the same conclusion that the crystal growth of MQW with abrupt interfaces is difficult without inserting interlayers. Therefore, the discussion and the conclusion in the article [1] are not affected by the error.

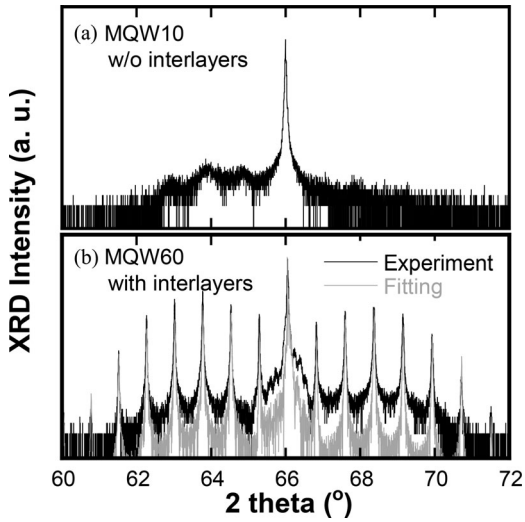


Fig. 3.

References

[1] H. Fujii, Y. Wang, K. Watanabe, M. Sugiyama, and Y. Nakano, "High-aspect ratio structures for efficient light absorption and carrier transport in InGaAs/GaAsP multiple quantum well solar cells," *IEEE J. Photovoltaics*, vol. 3, no. 2, pp. 859–867, Apr. 2013.

Manuscript received November 28, 2014; accepted December 8, 2014. Date of publication December 30, 2014; date of current version February 18, 2015.
Digital Object Identifier 10.1109/JPHOTOV.2014.2382980